EFFECTIVE COMPACT ACCELERATING STRUCTURES FOR HEAVY IONS

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Abstract

The well known interdigital IH structure is now widely used for acceleration of heavy ions in low \( \beta \) range. Using the main idea of the IH cavities - transformation of the transverse rf voltage into longitudinal accelerating one, but differing in realization of this principle, several rf structures are considered.

In comparison with the IH cavities, the proposed versions originally have practically uniform field distribution along beam axis and no problems with end walls. With the small outer tank diameter, the effective shunt impedance is high enough. The design of the structures and preliminary results of optimization are presented.

1 INTRODUCTION

For acceleration of charged particles in low velocity range (\( \beta \leq 0.1 \)) it is usually to apply InterDigital structures (ID). Let remember the main idea of the ID. There should be two conductors (electrodes) parallel to the beam axis. If one will supply rf voltage to these conductors, then rf electric field will be generated between electrodes, perpendicularly to the beam axis and no acceleration is possible. But, if drift tubes through short stems will be connected to these conductors in turn, then rf voltage will be between drift tubes, generating longitudinal accelerating field. So, drift tubes convert ‘perpendicular’ rf field into ‘longitudinal’ one.

Let remember the idea of another classical device - Radio Frequency Quadrupol (RFQ). There should be four conductors (electrodes) parallel to the beam axis. To provide quadrupol electric field distribution, one needs to supply rf voltage with opposite signs to neighboring conductors.

In the complete device there should be not only conductors, but also the resonant system to provide rf voltage between conductors. RFQ and ID structures differ in the utilization of the rf voltage, but may be very similar in resonant system to provide it. At least, if there is the solution for RFQ cavity, one can easy adapt it to ID structure.

Below options of cavities, known before for RFQ, are considered for ID applications.

2 DIFFERENT RESONANT SYSTEMS

This section comprises brief review of existing resonant systems, suitable for ID and RFQ structures, together with proposals given. The resonant systems both with distributed electrodynamic parameters and with lumped ones may be used both for RFQ and ID realizations.

3 H-TYPE CAVITIES

H-type cavities are now well known both for RFQ and for ID (IH structure). The example of application practically the same (in design) cavity both for IH and for RFQ is given in [1].

H-cavity is the system with distributed parameters. Instead of the electric field is strongly concentrated between conductors, the magnetic field is distributed more or less uniform in the remaining cavity volume. The original mode has longitudinal magnetic field and can not exist without variation along the cavity length (if one use simple end plates). To equalize field distribution, one should provide undercuts in vanes and girders near end plates. With modern software the problem of design for end regions simplifies [2], but some times configuration of girders remains complicated.

Another problems is also associated with end plates. For short cavities, when the cavity length is comparable with the cavity diameter, additional rf losses in end plates, where magnetic flux turns, lead to the reduction in shunt impedance.

Nevertheless, IH structure is good investigated, developed, there are solutions for problems and question is only price of solutions.

4 SPLIT RING RESONANT SYSTEM

Let consider resonant systems, which are more close to quaterwave oscillators. Both in RFQ and in ID conductors provide the capacitive part and one needs only add inductive part to complete the resonant circuit. Different solutions for inductive part are possible.
The Split Ring RFQ cavity is now under development in TRIUMF [3]. We propose the Split Ring Interdigital Structure (SRIS), Fig. 1.

Let define regular effective shunt impedance of the structure \( Z'_e \) as the effective shunt impedance of uniform periodical structure, consisting from similar modules. The length of the module \( L_m \) is the subject for choice and depends on tolerable tilt in difference of rf potential between electrodes. The potential difference between conductors is larger and the end of the module then in the middle, where conductors are connected to the ring. This tilt depends on \( L_m \) and capacitive loading due to drift tubes. The capacitive loading due to drift tubes depends on number of drift tubes per unit length and dimensions of drift tubes. The results of numerical simulations with MAFIA shows, that for \( L_m \approx 0.06 \lambda \), where \( \lambda \) is the operating wavelength, this tilt is less than 2% for \( 0.015 \leq \beta \leq 0.06 \) and any reasonable tube dimensions. With increasing \( L_m \) the tilt rise very fast, especially for higher \( \beta \) (to 5% \( \div \) 15% for \( L_m \approx 0.12 \lambda \)), providing upper limit for \( L_m \).

The SRIS has high effective shunt impedance. The dependencies of \( Z'_e \) vs \( \beta \) are shown in Fig. 2. All results of numerical simulation are given (if it is not defined specially) for operating frequency \( f_0 = 105 \text{MHz} \), \( L_m = 0.06 \lambda \), drift tube diameter \( 2r_t = 2a + 1.0 \text{cm} \), where \( 2a \) is aperture diameter and conductors diameter \( 2r_c = 3.8 \text{cm} \).

The SRIS cavity diameter \( 2R_e \) slightly rise from \( 2R_e = 52 \text{cm} \), \( \beta = 0.015 \) to \( 2R_e = 62 \text{cm} \), \( \beta = 0.06 \).

**5 POST RESONANT SYSTEM**

The Post RFQ cavity was realized [4] in Variable Energy RFQ option. With movable plate one can change effective length of the posts, changing the resonant frequency and, as the result, changing designed the cavity.

The Post Interdigital Structure (PIS), Fig. 3, also permits such option with the same question in rf contact between the plate and the posts. At the Fig. 3 one half of the structure period (from the middle of one post to the middle of next) is shown.

In comparison with SRIS, PIS has smaller cavity diameter \( (2R_e = 40 \text{cm}, \beta = 0.02) \). Effective shunt impedance remains high \( (Z'_e = 687 \text{M}\Omega/m, \beta = 0.02, 2r_a = 1.0 \text{cm}) \).

**6 SPIRAL RESONANT SYSTEM**

The spiral cavities for RFQ applications are considered in [5]. Following to our approach, the Spiral Interdigital Structure (SIS) may be developed. One can imagine transformation of all posts in PIS (Fig. 3) into spirals, resulting in spiral-type resonant system. This structure has smallest cavity diameter in comparison with SRIS and PIS. For operating frequency \( f_0 = 105 \text{MHz} \) the cavity is diameter very small, providing difficulties with placement of conductors and drift tubes. For this structure frequency range \( 20 \div 60 \text{MHz} \) is more comfortable. In comparison with resonant systems “one turn of the spiral to one drift tube” [6], SIS has essentially higher shunt impedance, because one spiral serves for several drift tubes and total rf losses are associated mainly with rf losses in spirals.

**7 DISCUSSION**

All structures considered above have very high \( Z'_e \). To get it, one should minimize capacitive load. In all calculations simple cylindrical drift tubes were considered with gap ration \( \alpha = 0.5 \). In reality, the shape of the drift tube should be chosen as the compromise to minimize maximum electric field on the surface \( E_s \), to minimize capacitance (taking into account the stem for support) and to have large transit time factor \( T \). Diameter of conductors should be as small as possible but providing possibility for cooling channel inside. Distribution of rf losses at elements differs no so strong for different structures. For \( L_m = 0.06 \lambda \) rf losses at drift tubes (including short stems) are \( \approx (5\% \div 8\%) \), at conductors - \( \approx (20\% \div 28\%) \), at the cylindrical wall - \( \approx (14\% \div 20\%) \). Main part of rf losses takes place at the ring (SRIS), post (PIS) or spiral (SIS).
It is not necessary to have complicated shape (with two radii) for ring or post. These elements with smooth shape provide practically the same value of $Z_e$.

All structures considered have their own particularities. The Split Ring Structure has very high shunt impedance. Because there are no rf current along the supporting leg (Fig. 1), there are no rigid requirements for rf contact between the leg and outer cavity wall. It simplifies procedure of the structure adjustment.

By using Post Structure, variable energy structure may be developed. The Spiral Structure may be used for low frequency range. For all structures electric field is concentrated between drift tubes and magnetic field is concentrated near inductive elements. This case end walls of the cavity do not disturb parameters of the structure.

Both short and long cavities may be with using SRIS. The example of short nine gap (8 total gaps and 2 reduced gaps near end walls) cavity with one ring is shown in Fig. 4, $L_m = 0.1\lambda, \beta = 0.02, 2a = 1.0\, \text{cm}, 2r_c = 2.0\, \text{cm}, Z_e = 756\, \text{M}\Omega/m$. This case reduction in $Z_e$ is associated mainly not with end walls, but with nonsymmetry. One conductor carries 5 drift tubes and another only 4. It provides nonsymmetry in the distribution of magnetic field and additional rf currents along the leg. The symmetrical ten gaps cavity has higher shunt impedance.

Long cavity may have several modula (Fig. 5). Each modula should be designed for his own average $\beta$, because with increasing of $\beta$ capacitive load decreases and outer radius of the ring increases. Differing from RFQ cavity, it looks not reasonable to connect modula directly thorough conductors. The coupling with longitudinal electric field is sufficient. Each module should be equipped with own tuner. With appropriate tuning of own frequency for each module (keeping the frequency of the cavity at the designed value), one can adjust increased rf voltage at modula with higher $\beta$. Because average (along structure period) electric field is inverse proportional to the period length (to $\beta$), increased voltage at modula with higher $\beta$ leads to constant average electric field along the cavity.

### 8 CONCLUSION

In this paper, developing idea of interdigital line, several accelerating structures are considered. All this structures have high effective shunt impedance and small transverse dimensions. For every structure there is RFQ analog. It allows to provide ‘uniform’ accelerating system by using RFQ initially and ID as extension with the same type of the resonant system. Such approach allows to use similar scientific, technical and technological solutions both for RFQ and for ID part, leading to reduction in total costs for development and production of the system.

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### 10 REFERENCES